

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \text{ max}}$	$I_D$ $T_A = +25^\circ\text{C}$
30V	29m $\Omega$ @ $V_{GS} = 10\text{V}$	5.6A
	35m $\Omega$ @ $V_{GS} = 4.5\text{V}$	4.8A

## Description

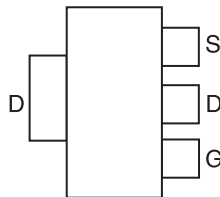
This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

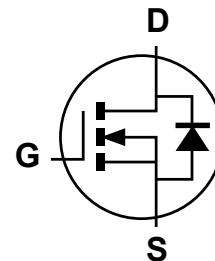
- DC Motor Control
- DC-AC Inverters



Top View



Pin Out - Top View



Equivalent Circuit

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

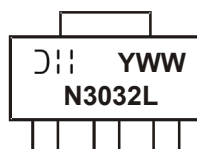
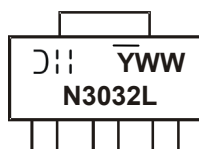
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (approximate)

## Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMN3032LE-13	Standard	SOT223	2,500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



⌋|| = Manufacturer's Marking  
 N3032L = Marking Code  
 YWW = Date Code Marking for SAT (Shanghai Assembly/ Test site)  
 YWW = Date Code Marking for CAT (Chengdu Assembly/ Test site)  
 Y or Y = Year (ex: 3 = 2013)  
 WW = Week (01 - 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C	5.6	A
	T <sub>A</sub> = +70°C	4.1	A
Maximum Continuous Body Diode Forward Current (Note 5)	T <sub>C</sub> = +25°C	15.4	A
	T <sub>C</sub> = +70°C	12.1	A
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	1.5	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)	I <sub>DM</sub>	25	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.8
		T <sub>A</sub> = +70°C	1.1
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	69	°C/W
Total Power Dissipation (Note 5)	P <sub>D</sub>	14	W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	8.7	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	—	2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	22	29	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.2A
		—	27	35		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.8A
Forward Transfer Admittance	Y <sub>fs</sub>	—	7	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 5.8A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.5	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	498	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	52	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	45	—		
Gate Resistnace	R <sub>g</sub>	—	2.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	11.3	—	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 5.8A
Gate-Source Charge	Q <sub>gs</sub>	—	1.4	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.1	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	2.3	—	ns	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 2.6Ω, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>r</sub>	—	3.9	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	10	—		
Turn-Off Fall Time	t <sub>f</sub>	—	1.9	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

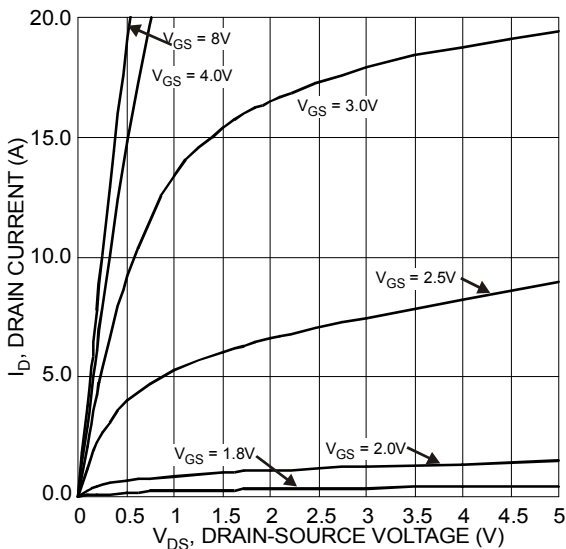


Figure 1 Typical Output Characteristic

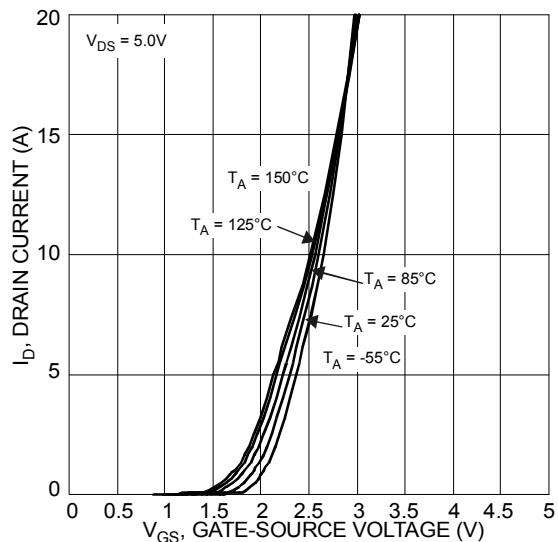


Figure 2 Typical Transfer Characteristics

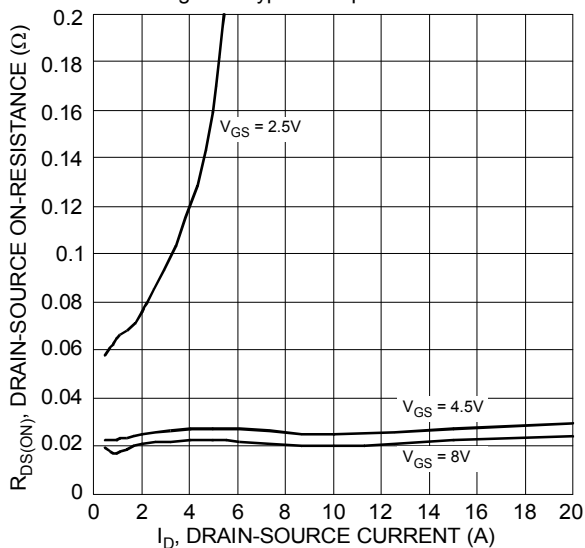


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

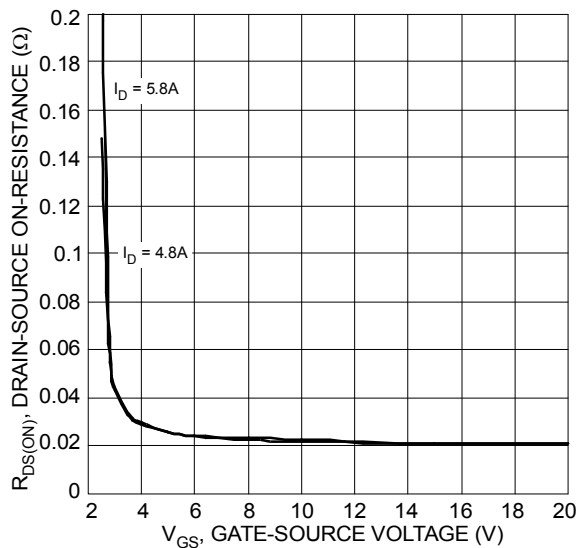


Figure 4 Typical Transfer Characteristic

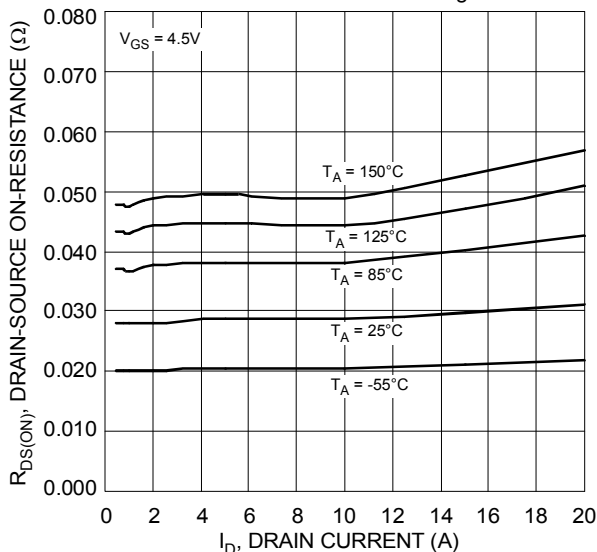


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

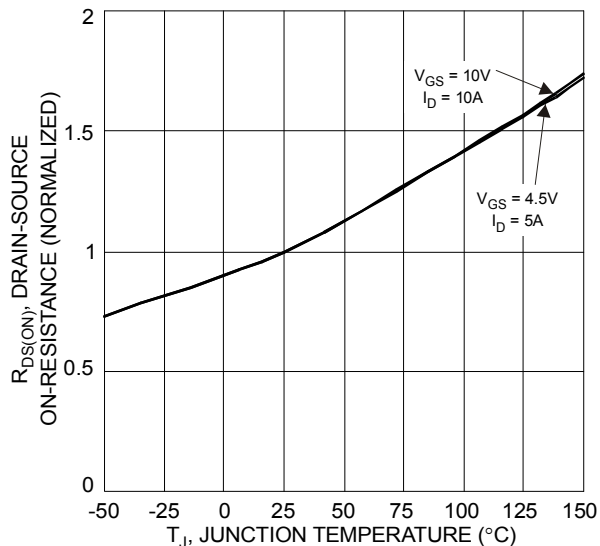
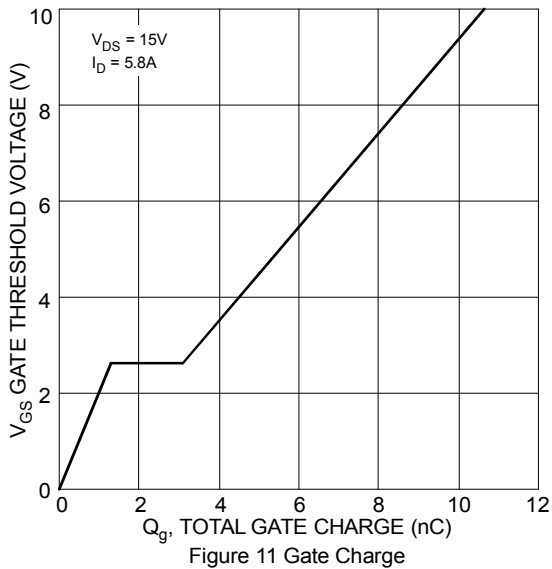
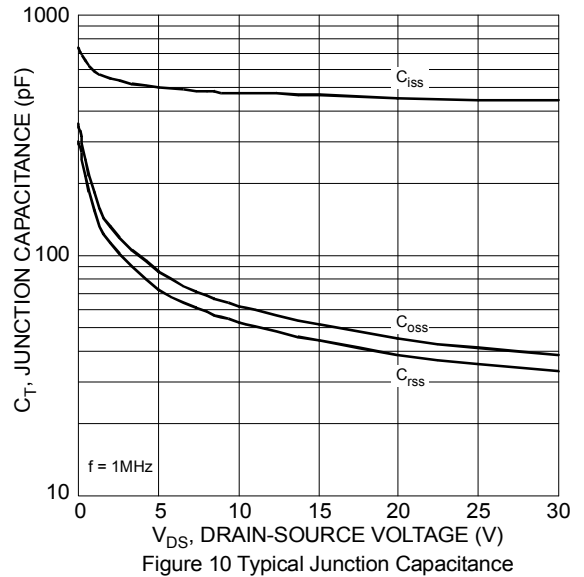
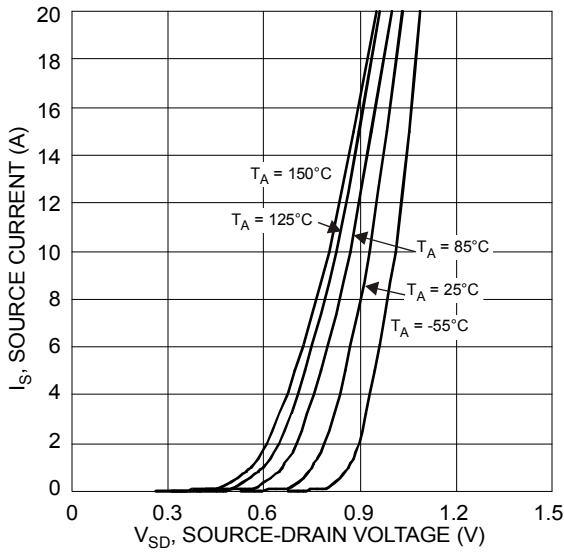
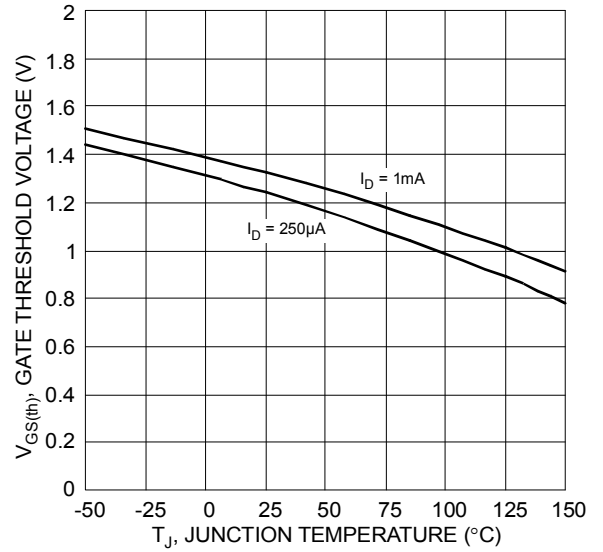
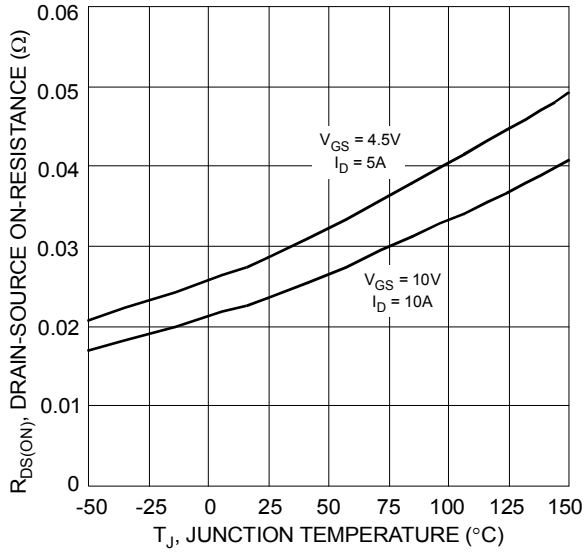
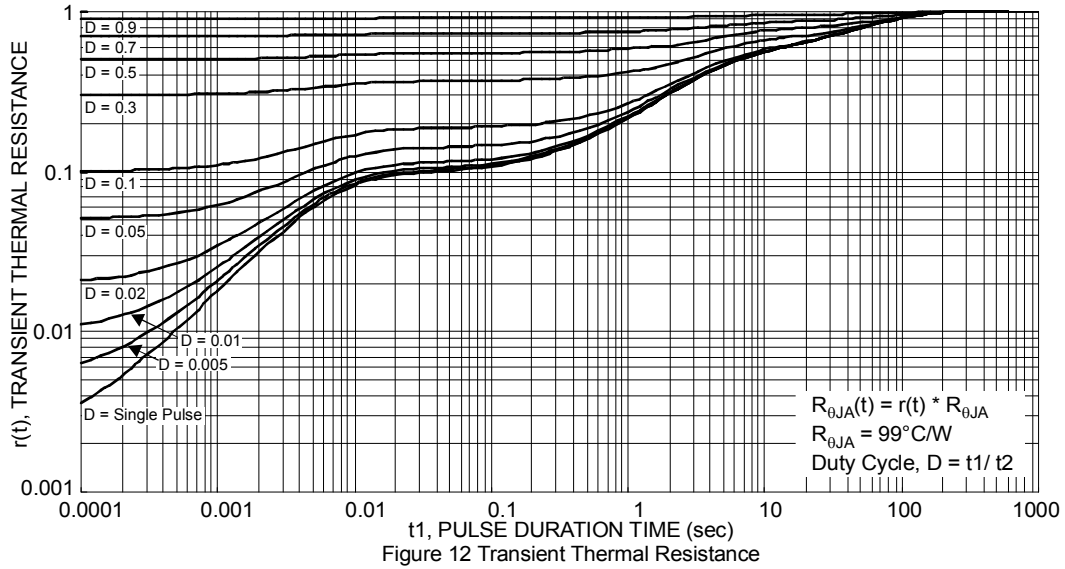


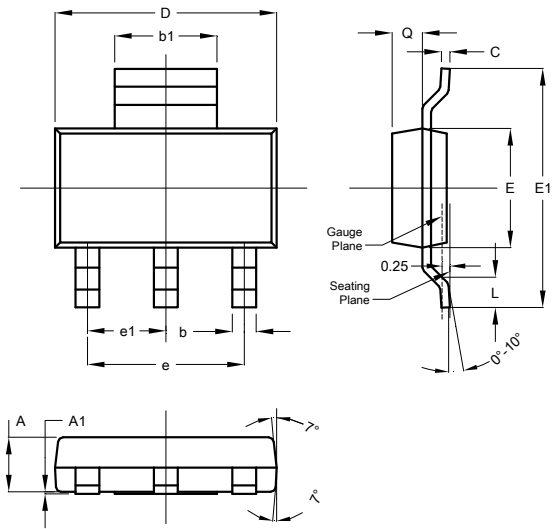
Figure 6 On-Resistance Variation with Temperature





**Package Outline Dimensions**

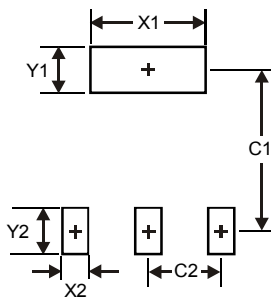
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3

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